

IIN THE CLAIMS

Pursuant to 37 CFR §121(c), the claim listing, including the text of the claims, will serve to replace all prior versions of the claims, in the application.

Please amend claims 1 and 3 and cancel claim 4 without disclaiming its subject matter to read as follow:

1 Claims 1-6. (Canceled).

1 7. (Currently Amended) A process for preparing a magnesium titanate oxide film
2 implant, comprising:
3 irradiating UV light on an implant body made of titanium or a titanium alloy in distilled
4 water for more than 2 hours;
5 dipping the UV light-irradiated implant body in an electrolyte solution containing
6 magnesium, the electrolyte solution having a concentration ranging from 0.01M to 1.0M; and
7 coating a magnesium titanate oxide film on the dipped implant body by anodic oxidation
8 at a voltage of 60 to 500V.

1 8. (Original) The process as set forth in claim 7, wherein the electrolyte solution is a
2 single or mixed solution containing magnesium.

1 9. (Canceled).

1 10. (Previously Presented) The process as set forth in claim 7, wherein the electrolyte
2 solution has a pH of 3.0 to 12.5.

1 11. (Previously Presented) The process as set forth in claim 7, wherein the current density
2 for performing the anodic oxidation is within the range of 30 to 4000 mA/cm².

12. (Canceled).

13. (Previously Presented) The process as set forth in claim 8, wherein the electrolyte solution has a pH of 3.0 to 12.5.

14. (Previously Presented) The process as set forth in claim 8, wherein the current density for performing the anodic oxidation is within the range of 30 to 4000 mA/cm².

Claims 15-17. (Canceled).

18. (Currently Amended) A process for preparing a magnesium titanate oxide film implant ~~as set forth in claim 1~~, comprising:

irradiating UV light on the implant body made of titanium or a titanium alloy in distilled water for more than two hours;

dipping the UV light-irradiated implant body in an electrolyte solution containing magnesium, having a pH of between 3.0 to 12.5 and a concentration ranging between 0.01M to 1.0M; and

coating a magnesium titanate oxide film on the dipped implant body by anodic oxidation within a range of between 30 ~~mA/cm²~~ mA/cm² and 4000 ~~mA/cm²~~ mA/cm², at a voltage of between 60V to 500V to prepare the magnesium titanate implant comprising the implant body containing said titanium or said titanium alloy, and the magnesium titanate oxide film formed on the surface of the said implant body, the magnesium titanate oxide film comprising an upper porous layer and a lower barrier layer.

19. (Canceled).

20. (Canceled).